SEMICONDUCTOR LASER ELEMENT AND ITS MANUFACTURE

Patent number: JP11312840
Publication date: 1999-11-09
Inventor: HATA TOSHIO; ITO SHIGETOSHI
Applicant: SHARP CORP
Classification:
- international: H01S3/18
- european:
Application number: JP19980117948 19980428
Priority number(s):

Also published as
US632020

Abstract of **JP11312840**

PROBLEM TO BE SOLVED: To provide a technology for extending the element life of a semiconductor laser element of gallium nitride compound semiconductor and for reducing series resistance of the semiconductor element.
SOLUTION: This is a gallium nitride compound semiconductor laser element in which a conductive selective growth mask 104 is formed on a gallium nitride compound semiconductor, on which at least a pair of clad layer 106 and an active layer 107 are formed. Here, with an element structure for which the conductive selective growth mask 104 functions as a current path, a reliable current preventivng gallium nitride compound semiconductor laser element with reduced threshold current is realized.